Ordering number: EN 1017B

SANYO No.1017B

2SC3088

NPN Triple Diffused Planar Silicon Transistor

FOR SWITCHING REGULATORS

Features

- High breakdown voltage(V_{CBO}≧800V)
- Fast switching speed.
- Wide ASO.

Absolute Maximum Ratings at Ta=25°C

				unit
Collector-to-Base Voltage	V_{CBO}		800	V
Collector-to-Emitter Voltage	V_{CEO}		500	V
Emitter-to-Base Voltage	V_{EBO}		7	V
Collector Current	I_C		4	A
Peak Collector Current	i_{cp}	PW≦300μs, Duty Cycle≦10%	8	A
Base Current	I_B		1.5	A
Collector Dissipation	P_C		2.5	W
		Tc=25°C	60	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

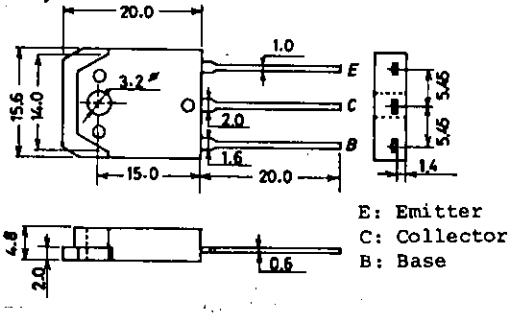
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB}=500V, I_E=0			10	μA
Emitter Cutoff Current	I_{EBO}	V_{EB}=5V, I_C=0			10	μA
DC Current Gain	$h_{FE}(1)$	V_{CE}=5V, I_C=0.3A	15*		50*	
	$h_{FE}(2)$	V_{CE}=5V, I_C=1.5A	8			
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=1.5A, I_B=0.3A			1.0	V
B-E Saturation Voltage	$V_{BE(sat)}$	I_C=1.5A, I_B=0.3A			1.5	V
Gain-Bandwidth Product	f_T	V_{CE}=10V, I_C=0.3A		18		MHz
Output Capacitance	c_{ob}	V_{CB}=10V, f=1MHz		40		pF
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C=1mA, I_E=0	800			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=1mA, R_{BE}=∞	500			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E=1mA, I_C=0	7			V
C-E Sustain Voltage	$V_{CEO(sus)}$	I_C=4A, I_B=0.8A, L=50μH	500			V
C-E Sustain Voltage	$V_{CEX(sus)}$ (1)	I_C=4A, I_{B1}=0.8A, L=200μH, I_{B2}=-0.8A, clamped	500			V
C-E Sustain Voltage	$V_{CEX(sus)}$ (2)	I_C=0.6A, I_{B1}=0.12A, L=200μH I_{B2}=-0.12A, clamped	550			V

Continued on next page.

*: The $h_{FE(1)}$ of the 2SC3088 is classified as follows. When specifying the $h_{FE(1)}$ rank, specify two ranks or more in principle.

15 L 30	20 M 40	30 N 50

Package Dimensions 2022
(unit:mm)



E: Emitter
C: Collector
B: Base

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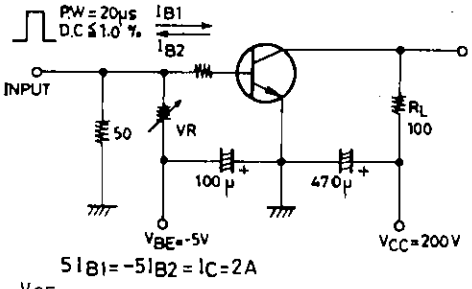
			min	typ	max	unit
Turn-ON Time	t_{on}	I_C=2A, I_{B1}=0.4A, I_{B2}=-0.4A, R_L=100ohms, V_{CC}=200V			1.0	μs
Storage Time	t_{stg}	" "			3.0	μs
Fall Time	t_f	" "			1.0	μs

Switching Time Test Circuit



$5I_{B1}=-5I_{B2}=I_C=2A$

Unit (Resistance : Ω, Capacitance : F)